

# QM600HD-M

HIGH POWER SWITCHING USE  
NON-INSULATED TYPE

QM600HD-M



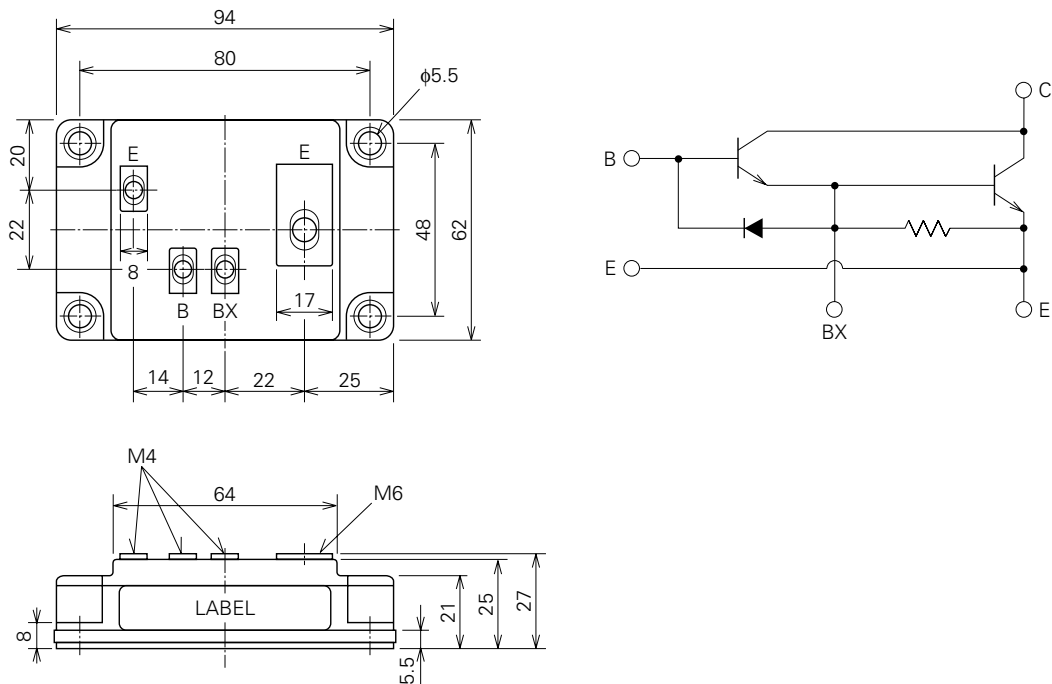
- **IC** Collector current ..... **600A**
- **VCEX** Collector-emitter voltage ..... **350V**
- **hFE** DC current gain ..... **500**
- **Non-Insulated Type**

## APPLICATION

Robotics, Forklifts, Welders

## OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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**ABSOLUTE MAXIMUM RATINGS** (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>CEX (SUS)</sub>	Collector-emitter voltage	I <sub>C</sub> =1A, V <sub>EB</sub> =2V	350	V
V <sub>CEX</sub>	Collector-emitter voltage	V <sub>EB</sub> =2V	350	V
V <sub>CBO</sub>	Collector-base voltage	Emitter open	400	V
V <sub>EBO</sub>	Emitter-base voltage	Collector open	10	V
I <sub>C</sub>	Collector current	DC	600	A
-I <sub>C</sub>	Collector reverse current	DC (forward diode current)	—	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	2080	W
I <sub>B</sub>	Base current	DC	15	A
-I <sub>CSM</sub>	Surge collector reverse current (forward diode current)	Peak value of one cycle of 60Hz (half wave)	—	A
T <sub>j</sub>	Junction temperature		-40~+150	°C
T <sub>stg</sub>	Storage temperature		-40~+125	°C
V <sub>iso</sub>	Isolation voltage	Charged part to case, AC for 1 minute	—	V
—	Mounting torque	Main terminal screw M6	1.96~2.94	N·m
			20~30	kg·cm
		Mounting screw M5	1.47~1.96	N·m
			15~20	kg·cm
		B(E) terminal screw M4	0.98~1.47	N·m
			10~15	kg·cm
—	Weight	BX terminal screw M4	0.98~1.47	N·m
			10~15	kg·cm
—	Weight	Typical value	420	g

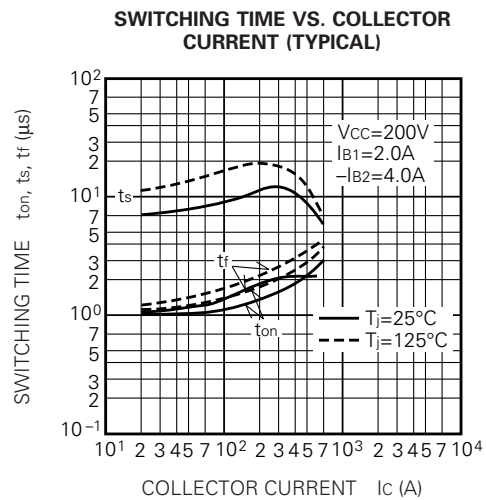
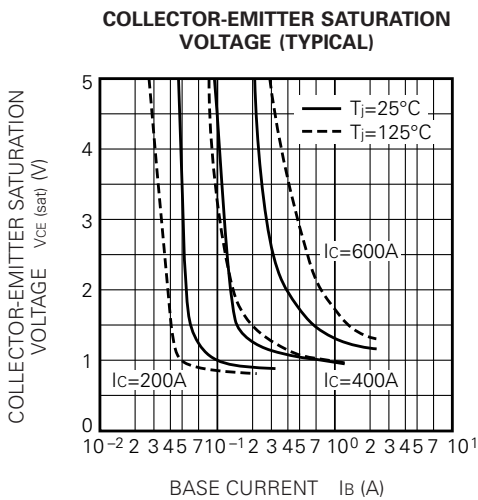
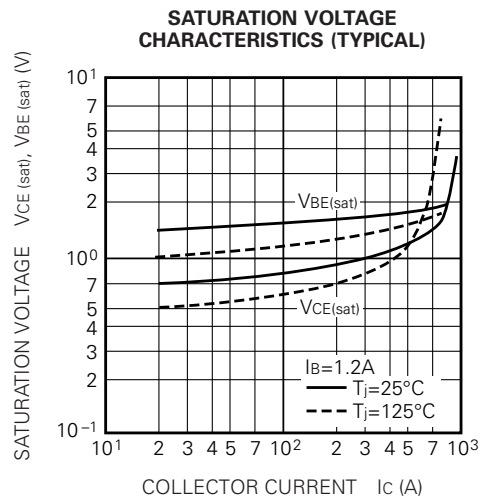
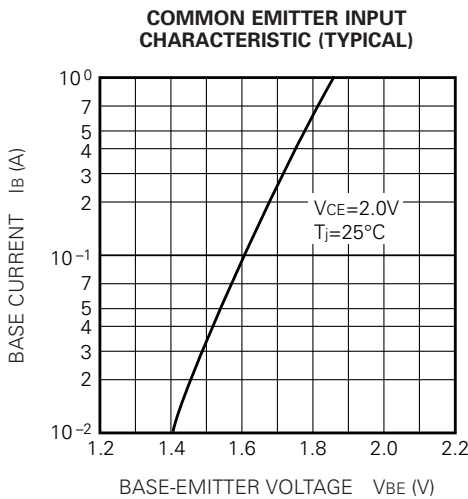
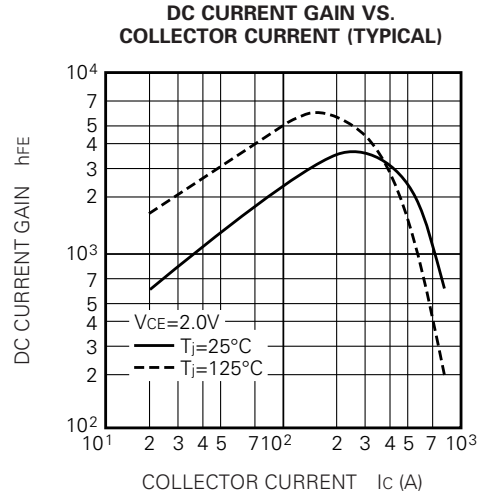
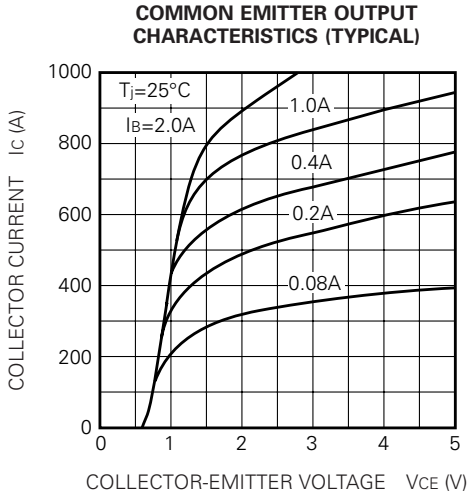
**ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I <sub>C</sub> EX	Collector cutoff current	V <sub>CE</sub> =350V, V <sub>EB</sub> =2V	—	—	2.0	mA
I <sub>C</sub> BO	Collector cutoff current	V <sub>CB</sub> =400V, Emitter open	—	—	2.0	mA
I <sub>E</sub> BO	Emitter cutoff current	V <sub>EB</sub> =10V	—	—	800	mA
V <sub>CE (sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =600A, I <sub>B</sub> =1.2A	—	—	2.0	V
V <sub>BE (sat)</sub>	Base-emitter saturation voltage		—	—	2.5	V
-V <sub>CEO</sub>	Collector-emitter reverse voltage	-I <sub>C</sub> =600A (diode forward voltage)	—	—	—	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =600A, V <sub>CE</sub> =2V	500	—	—	—
t <sub>on</sub>	Switching time	V <sub>CC</sub> =200V, I <sub>C</sub> =600A, I <sub>B1</sub> =2A, -I <sub>B2</sub> =4A	—	—	3.0	μs
t <sub>s</sub>			—	—	15	μs
t <sub>f</sub>			—	—	3.0	μs
R <sub>th (j-c) Q</sub>			Thermal resistance (junction to case)	Transistor part	—	—
R <sub>th (j-c) R</sub>	Diode part	—		—	—	°C/W
R <sub>th (c-f)</sub>	Contact thermal resistance (case to fin)	Conductive grease applied	—	—	0.05	°C/W

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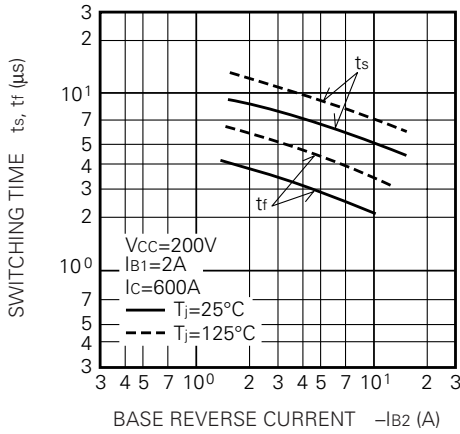
## PERFORMANCE CURVES



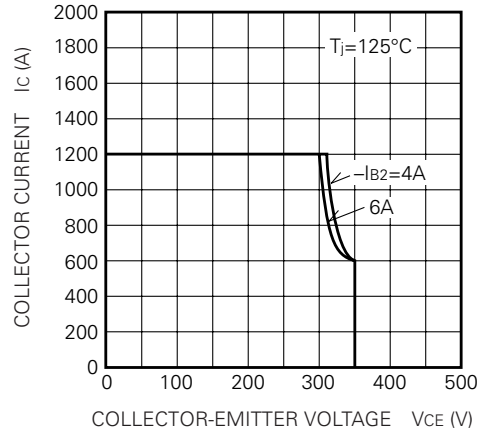
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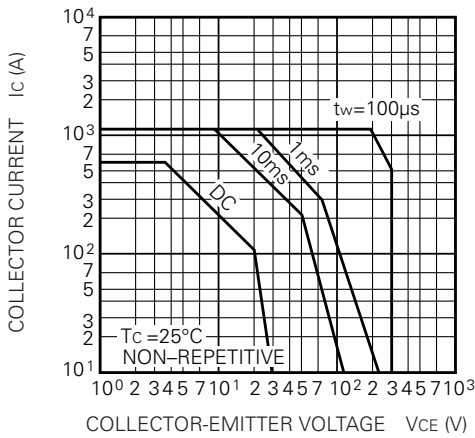
SWITCHING TIME VS. BASE CURRENT (TYPICAL)



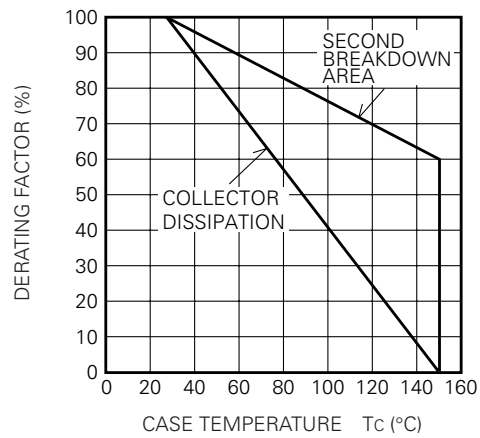
REVERSE BIAS SAFE OPERATING AREA



FORWARD BIAS SAFE OPERATING AREA



DERATING FACTOR OF F. B. S. O. A.



TRANSIENT THERMAL IMPEDANCE CHARACTERISTIC (TRANSISTOR)

